

IN THE CLAIMS:

In accordance with 37 C.F.R. § 1.121(c), please amend the claims as set forth below.

Please amend Claims 1-12 in the following manner:

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1. (Amended) A method of forming a by-pass capacitor on a multi-level metallization device, said method comprising:
forming a first electrode in a first dielectric layer of said multi-level metallization device;
depositing a substantially thin insulator layer over said first dielectric layer of said multi-level metallization device; and
forming a second electrode in a second dielectric layer, wherein said second dielectric layer is formed over said substantially thin insulator layer.

2. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 1, said method further comprising:
patterning said substantially thin insulator layer to substantially cover said first electrode; and
adjusting a thickness of said substantially thin insulator layer.

3. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 2, wherein a dielectric constant of said substantially thin insulator layer is substantially high.

4. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 3, wherein said substantially thin insulator layer includes silicon nitride.

5. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 3, wherein said thickness of said substantially thin insulator layer is between 50 and 100 angstroms. In it should be

6. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 3, wherein said dielectric constant of said substantially thin insulator layer is between 4 and 100.

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7. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 1, said method further comprising:
depositing the second dielectric layer over said substantially thin insulator layer; and
etching at least one via, said at least one via adapted to receive said second electrode.

8. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 7, said method further comprising:
polishing said second electrode.

9. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 1, wherein said forming said first electrode comprises:

etching said first electrode in the first dielectric layer of said multi-level metallization device.

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10. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 1, further comprising:

forming the first electrode in a parallel line configuration.

11. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 1, further comprising:

forming the second electrode in a parallel line configuration.

12. (Amended) The method of forming a by-pass capacitor on a multi-level metallization device according to claim 1, wherein said substantially thin insulator layer comprises a composite of materials.